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APPLICATION NO	. F	ILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO. 3646	
10/006,718		12/10/2001	Mitsuhiro Okuni	740819-711		
22204	7590	04/23/2003				
NIXON P	EABODY	, LLP	EXAM	EXAMINER		
8180 GREI SUITE 800)			VINH, LAN		
MCLEAN,	MCLEAN, VA 22102			ART UNIT	PAPER NUMBER	
				1765	3	
·			·	DATE MAILED: 04/23/2003		

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Ap	plicant(s)						
Office Action Summary		10/006,718		OKUNI, MITSUHIRO						
		Examin r		t Unit						
		Lan Vinh	170							
T	he MAILING DATE of this communication a				dress					
Period for Reply										
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely. - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). - Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b). Status										
1)⊠ F	Responsive to communication(s) filed on 1	<u> 10 December 2001</u> .	,							
_ ,	,	This action is non-fin-								
3)□ S	Since this application is in condition for all	owance except for for	mal matters, prose	ecution as to th O.G. 213	ne merits is					
closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213. Disposition of Claims										
4)⊠ Claim(s) 1-10 is/are pending in the application.										
4a) Of the above claim(s) is/are withdrawn from consideration.										
	5) Claim(s) is/are allowed.									
, —	laim(s) <u>1-10</u> is/are rejected.									
, 	laim(s) is/are objected to.	d/or election requirem	nent							
8)	laim(s) are subject to restriction and Papers	iaror electron requiren	, 4116							
• •	e specification is objected to by the Exam	niner.								
,	e drawing(s) filed on is/are: a) a		d to by the Examin	ier.						
	Applicant may not request that any objection t	o the drawing(s) be held	l in abeyance. See 3	37 CFR 1.85(a).						
11)[] Th	e proposed drawing correction filed on	is: a)∏ approve	d b)∏ disapprove	d by the Examir	ner.					
If approved, corrected drawings are required in reply to this Office action.										
12) 🗌 Th	e oath or declaration is objected to by the	e Examiner.								
-	der 35 U.S.C. §§ 119 and 120			n						
1	cknowledgment is made of a claim for for	eign priority under 35	U.S.C. § 119(a)-(d) or (f).						
a)⊠	All b) ☐ Some * c) ☐ None of:									
1	. Certified copies of the priority docum			No. 40000741	5					
	. Certified copies of the priority docum									
* Se	. Copies of the certified copies of the application from the Internationa e the attached detailed Office action for a	il Bureau (PCT Rule 1 I list of the certified co	7.2(a)). pies not received.							
	knowledgment is made of a claim for dom			(to a provision	al application).					
a) l	The translation of the foreign language tknowledgment is made of a claim for don	e provisional application	on has been receiv	/ed.						
Attachment(s										
2) Notice	of References Cited (PTO-892) of Draftsperson's Patent Drawing Review (PTO-948 ation Disclosure Statement(s) (PTO-1449) Paper No	4)	Interview Summary (P Notice of Informal Pat Other:	PTO-413) Paper N ent Application (P	o(s) TO-152)					

U.S. Patent and Trademark Office PTO-326 (Rev. 04-01)

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DETAILED ACTION

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 1, 6 are rejected under 35 U.S.C. 103(a) as being unpatentable over Miyoshi (US 5,801,101) in view of Kumihashi et al (US 5,368,685)

Miyoshi discloses a method for forming metal wiring by dry etching an aluminum-silicon copper alloy film in the plasma chamber using an etching gas mixture mainly comprises a chlorine gas (col 5, lines 25-28). Mioshi also discloses that t= pV/Q wherein t is the residence time of the gas in the chamber/gas stay time, p: the pressure in the chamber (Torr), V: chamber volume (I), Q: exhaustion amount (Torr.I/sec)/total etching gas flow (col 3, lines 15-25)

Unlike the instant claimed inventions as per claims 1, 6, Miyoshi does not disclose the specific values of the gas stay time/ the residence time of the gas in the chamber and the pressure in the chamber although Miyoshi discloses that the residence time of the gas/gas stay time can be changed by changing/adjusting the pressure in the chamber and the exhaustion amount/total etching gas flow (col 3, lines 32-35)

However, Kumihashi, in a method of dry etching, teaches changing the volume of the etching chamber and volume of the discharge/exhaust part to obtain a specific gas residence time (col 13, lines 11-15)

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Hence, one skilled in the art would have found it obvious to change/adjust Miyoshi's chamber pressure and the exhaustion amount/total flow rate by conducting routine experimentations to obtain the specific value of the gas stay time because Kumihashi serves as evidence that the gas stay time/ the residence time of the gas is a result variable. It has been held that the discovery of an optimum value for result effective variables is within the purview of routine experimentation by the person of ordinary skill in the art. In re Boesch, 617 F.2d 272, 276, 205 USPQ 215, 219 (CCPA 1980)

3. Claims 2, 4, 7, 9 are rejected under 35 U.S.C. 103(a) as being unpatentable over Miyoshi (US 5,801,101) in view of Kumihashi et al (US 5,368,685) and further in view of Nowak et al (US 6,220,201)

Miyoshi as modified by Kumihashi has been discussed above in paragraph 2. Unlike the instant claimed inventions as per claims 2, 4, 7, 9, Miyoshi and Kumihashi do not disclose the specific values of the wafer diameter and the chamber volume.

However, Nowak, in a method of high density plasma etching, teaches that the volume of the chamber changes depending on the size of the wafer (col 7, lines 23-25)

Thus, Novak serves as evidence that volume of the chamber and size/diameter of the wafer are result variable. It has been held that the discovery of an optimum value for result effective variables is within the purview of routine experimentation by the person of ordinary skill in the art. In re Boesch, 617 F.2d 272, 276, 205 USPQ 215, 219 (CCPA 1980)

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4. Claims 3, 5, 8, 10 are rejected under 35 U.S.C. 103(a) as being unpatentable over Miyoshi (US 5,801,101) in view of Kumihashi et al (US 5,368,685) and further in view of Nowak et al (US 6,220,201) and Hynecek (US 4,708,766)

Miyoshi as modified by Kumihashi and Novak has been discussed above in paragraph 3. Unlike the instant claimed inventions as per claims 3, 5, 8,10, Miyoshi, Kumihashi and Novak do not disclose the specific values of the total etching gas flow rate.

However, Hynecek, in a method of dry etching, teaches that the gas flow rate should be adjusted proportionally when the volume of the chamber changes (col 5, lines 26-29)

Hence, one skilled in the art would have found it obvious to change/adjust Miyoshi, Kumihashi and Novak chamber pressure by conducting routine experimentations to obtain the specific flow rate values because Hynecek serves as evidence that the gas flow rate is a result variable. It has been held that the discovery of an optimum value for result effective variables is within the purview of routine experimentation by the person of ordinary skill in the art. In re Boesch, 617 F.2d 272, 276, 205 USPQ 215, 219 (CCPA 1980)

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Conclusion

5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lan Vinh whose telephone number is 703 305-6302. The examiner can normally be reached on M-F 8:30-5:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Benjamin Utech can be reached on 703 308-3836. The fax phone numbers for the organization where this application or proceeding is assigned are 703 872-9310 for regular communications and 703 872-9311 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703 308-0661.

LV

April 10, 2003